

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the above-referenced application.

Listing of Claims:

1. (Currently amended) A semiconductor device, comprising:

an interconnect layer provided on a semiconductor substrate;

a protective film provided on said interconnect layer; [[and]]

an electrode pad provided on said protective film[.]; and

~~wherein said semiconductor device comprises~~ an anti-oxidizing layer containing a different element which is different from an element contained in said interconnect layer, said anti-oxidizing layer being disposed between said interconnect layer and said protective film, wherein said electrode pad is in electrical contact with said interconnect layer and is disposed on said protective film in a position to permit contact by a probe, and wherein said different element of said anti-oxidizing layer has a lower oxidation-reduction potential than that of said element contained in said interconnect layer, said anti-oxidizing layer being disposed on said interconnect layer to inhibit corrosion of said interconnect layer when an interface between said electrode pad and said interconnect layer is damaged by said probe.

2. (Original) The semiconductor device according to claim 1, wherein said interconnect layer is a copper-containing metal.

3. (Original) The semiconductor device according to claim 1, wherein said different element is a metal having lower oxidation-reduction potential than that of a metal contained in said interconnect layer.
4. (Original) The semiconductor device according to claim 3, wherein said different element is a group IV element or a group VI element in long form periodic table.
5. (Original) The semiconductor device according to claim 4, wherein said different element is Ti or Si.
6. (Original) The semiconductor device according to claim 1, wherein said protective film includes a Ti layer or a TiN layer.
7. (Original) The semiconductor device according to claim 1, wherein said anti-oxidizing layer is a layer where the upper part of said interconnect layer is modified, and comprises said different element and an element contained in said interconnect layer.

Claims 8 - 19 (Cancelled)

20. (New) A semiconductor device, comprising:
- an interconnect layer provided on a semiconductor substrate;
 - a protective film provided on said interconnect layer;
 - an electrode pad provided on said protective film; and
 - an anti-oxidizing layer containing a different element which is different from an element contained in said interconnect layer, said anti-oxidizing layer being disposed between said interconnect layer and said protective film, wherein said electrode pad is in electrical contact with said interconnect layer and is disposed on said protective film in a position to permit contact by a probe, and said anti-oxidizing layer being disposed on said interconnect layer to inhibit corrosion of said interconnect layer when an interface between said electrode pad and said interconnect layer is damaged by said probe.
21. (New) The semiconductor device according to claim 20, wherein said interconnect layer is a copper-containing metal.
22. (New) The semiconductor device according to claim 20, wherein said different element is a metal having lower oxidation-reduction potential than that of a metal contained in said interconnect layer.
23. (New) The semiconductor device according to claim 22, wherein said different element is a group IV element or a group VI element in a long form periodic table.

24. (New) The semiconductor device according to claim 23, wherein said different element is Ti or Si.
25. (New) The semiconductor device according to claim 20, wherein said protective film includes a Ti layer or a TiN layer.
26. (New) The semiconductor device according to claim 20, wherein said anti-oxidizing layer is a layer where the upper part of said interconnect layer is modified, and comprises said different element and an element contained in said interconnect layer.